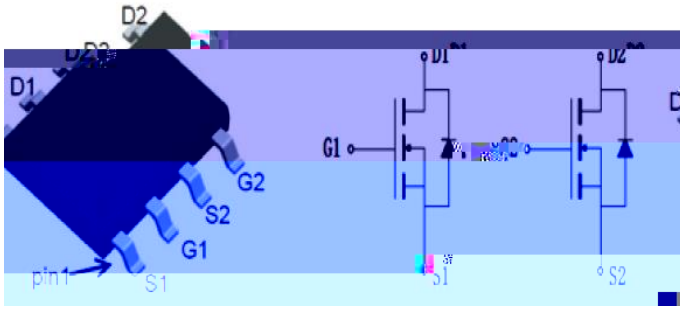




## N-Channel Enhancement Mode Field Effect Transistor



### Product Summary

$V_{DS}$	30V
$I_D$	8.5A
$R_{DS(ON)}$ ( at $V_{GS}=10V$ )	21mohm
$R_{DS(ON)}$ ( at $V_{GS}=4.5V$ )	35mohm
100% $V_{DS}$ Tested	

### General Description

Trench Power LV MOSFET technology





Typical Performance Characteristics

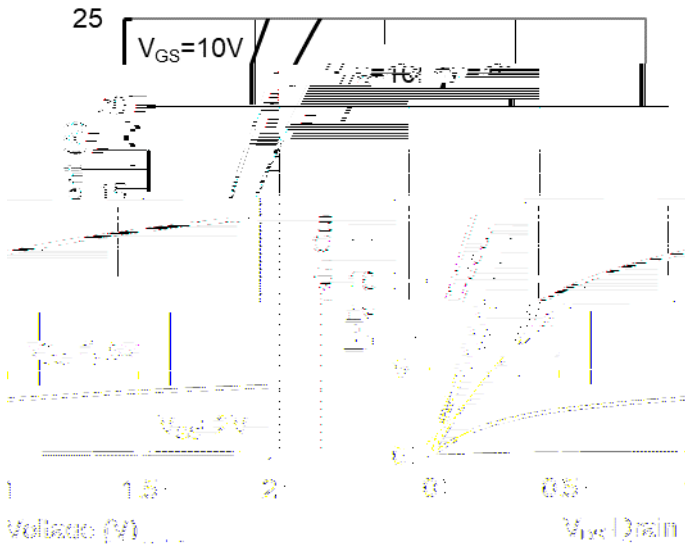


Figure1. Output Characteristics

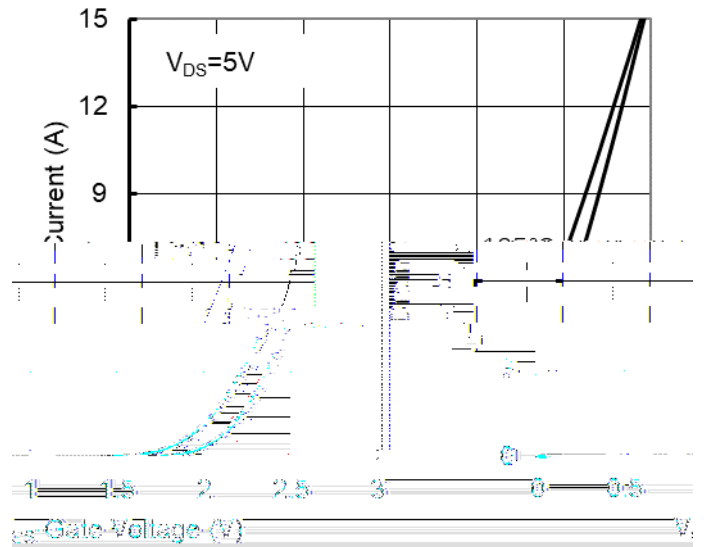


Figure2. Transfer Characteristics

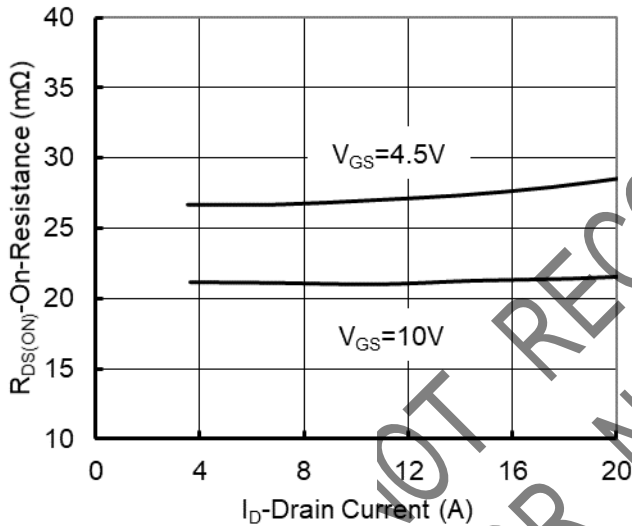


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

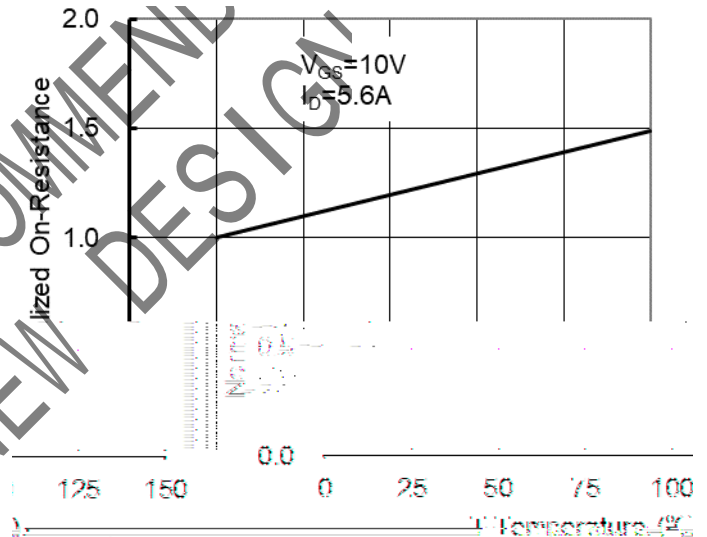


Figure 4: On-Resistance vs. Junction Temperature

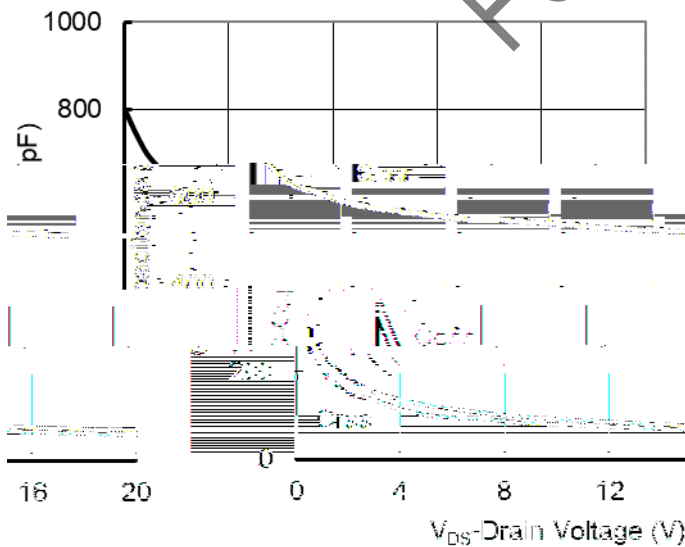


Figure5. Capacitance Characteristics

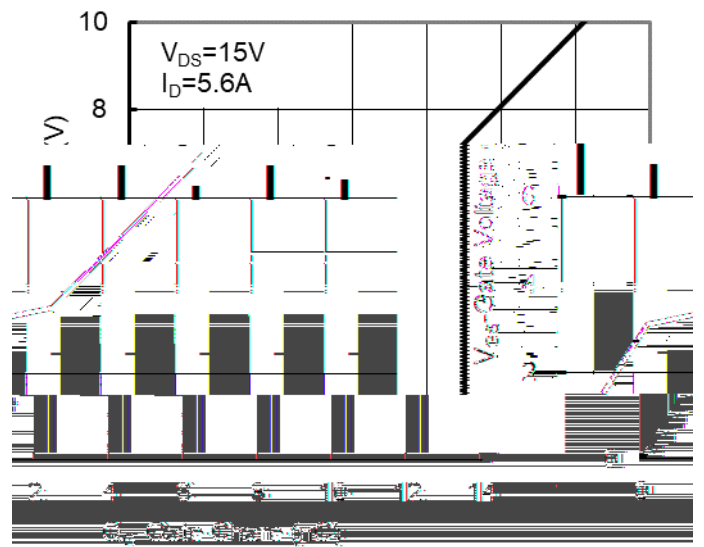
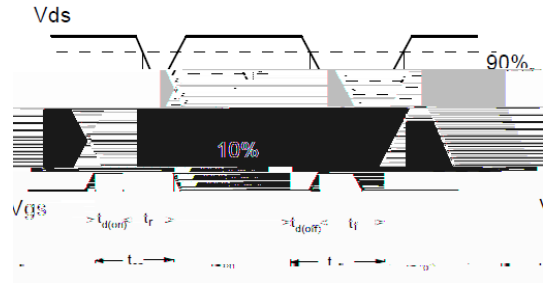
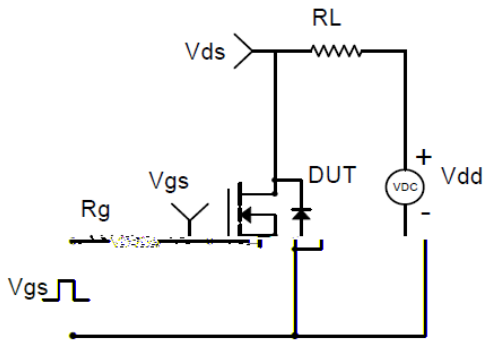


Figure6. Gate Charge

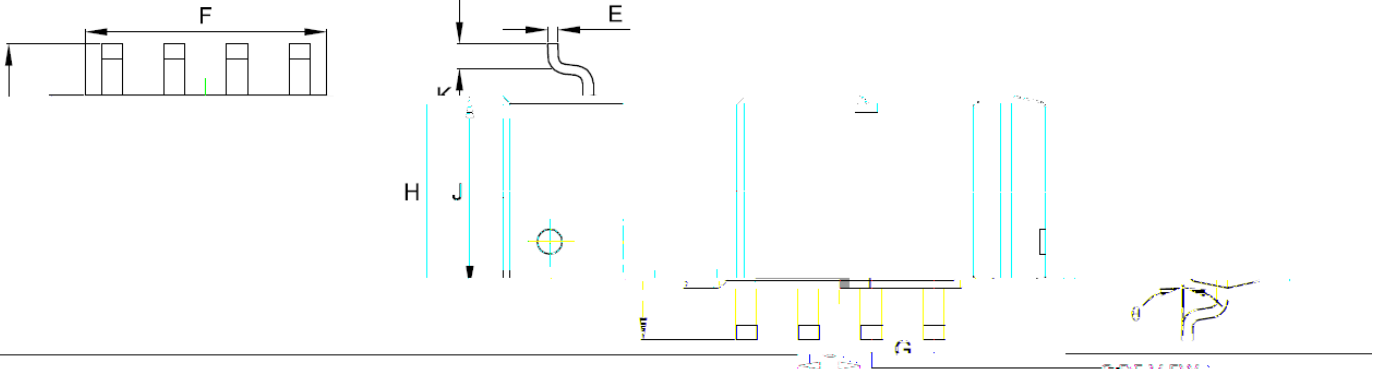




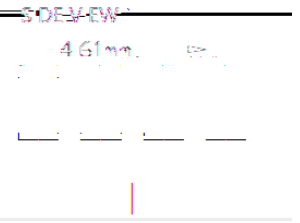
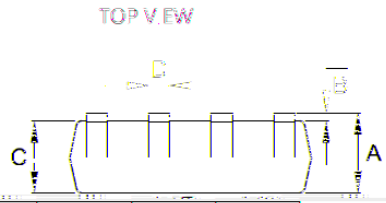
Resistive Switching



SOP-8 Package information



DIMENSIONS	MIN		MAX	
	MIN	MAX	MIN	MAX
A	0.058	0.069	1.950	1.730
B	0.004	0.010	0.100	0.230
C	0.353	0.061	1.350	1.550
D	0.013	0.020	0.330	0.510



	E	F	G	H	I	J	K
	0.07	0.00	0.00	0.25			
G	0.0503SC		1.2703SC				
J	0.150	0.157	3.900	4.000			
K	0.016	0.050	0.400	1.270			

NOT RECOMMEND FOR NEW DESIGN



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Disclaimer